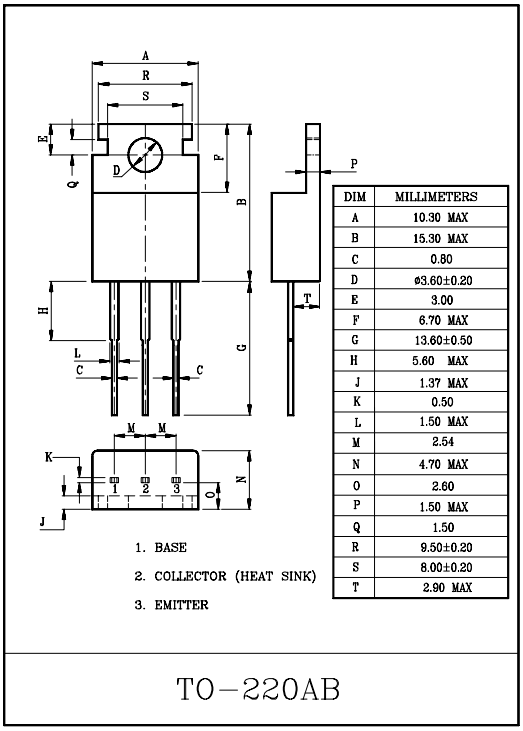
KTB595

TRIPLE DIFFUSED PNP TRANSISTOR

GENERAL PURPOSE APPLICATION.

FEATURES

- High Breakdown Voltage : V_{CEO}=-100V.
- Low Collector-Emitter Saturation Voltage.
  : $V_{CE(sat)}$=-2.0V(Max.)
- Complementary to KTD525.



DIM	MILLIMETERS
A	10.30 MAX
B	15.30 MAX
C	0.80
D	ø3.60±0.20
E	3.00
F	6.70 MAX
G	13.60±0.50
H	5.60 MAX
J	1.37 MAX
K	0.50
L	1.50 MAX
M	2.54
N	4.70 MAX
O	2.60
P	1.50 MAX
Q	1.50
R	9.50±0.20
S	8.00±0.20
T	2.90 MAX

TO-220AB

MAXIMUM RATINGS (Ta=25℃)

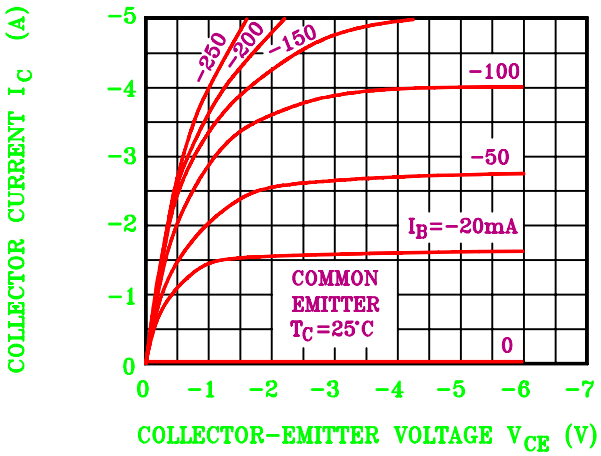
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-100	V
Collector-Emitter Voltage	V_{CEO}	-100	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-5	A
Emitter Current	I_E	5	A
Base Current	I_B	-0.5	A
Collector Power Dissipation (Tc=25℃)	P_C	40	W
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55~150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃)

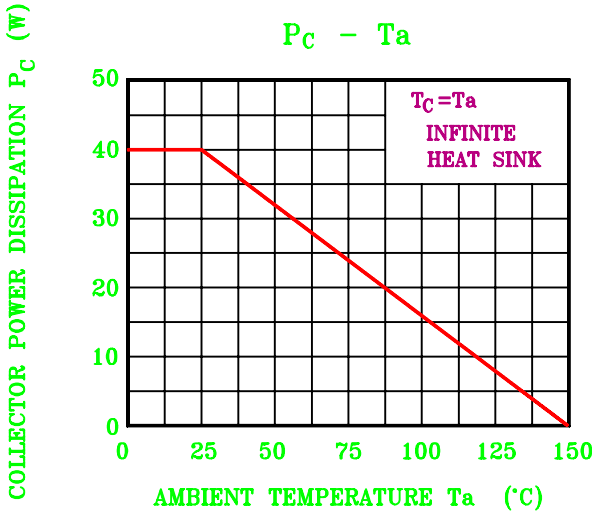
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB}=-100V, I_E=0	-	-	-100	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=-5V, I_C=0	-	-	-1.0	mA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=-50mA, I_B=0	-100	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=-10mA, I_C=0	-5.0	-	-	V
DC Current Gain	h_{FE}(1) (Note)	V_{CE}=-5V, I_C=-1A	40	-	240	
	h_{FE}(2)	V_{CE}=-5V, I_C=-4A	20	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-4A, I_B=-0.4A	-	-	-2.0	V
Base-Emitter Voltage	V_{BE}	V_{CE}=-5V, I_C=-4A	-	-	-1.5	V
Transition Frequency	f_T	V_{CE}=-5V, I_C=-1A	-	5.0	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz	-	270	-	pF

Note : h_{FE}(1) Classification R:40~80 , O:70~140 , Y:120~240

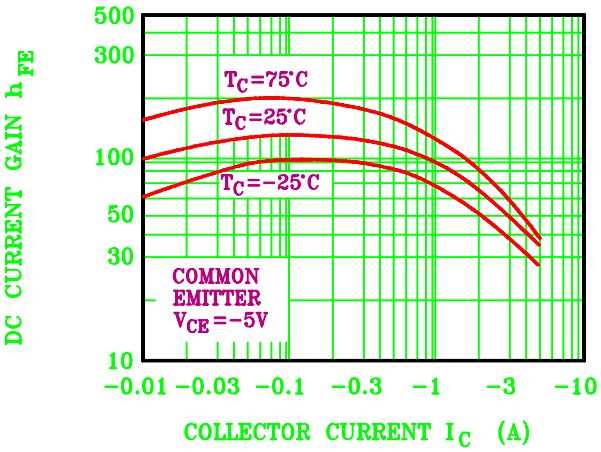
I_C – V_{CE}



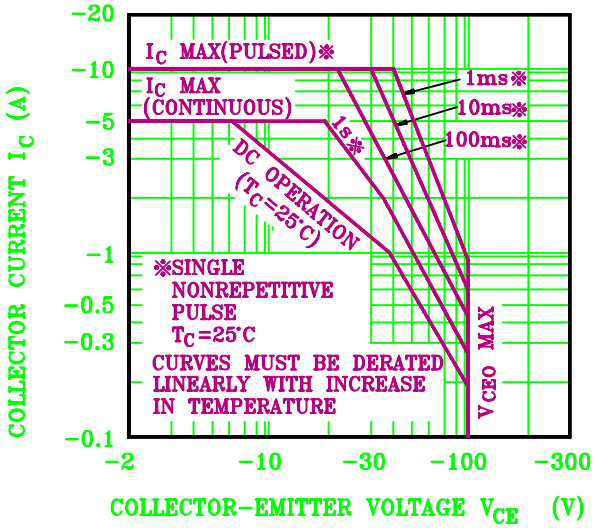
P_C – Ta



h_{FE} – I_C



SAFE OPERATING AREA



$V_{CE(sat)}$ – I_C